

## Product Summary

| BV <sub>DSS</sub> | R <sub>DS(ON)</sub> Max       | I <sub>D</sub> Max<br>T <sub>A</sub> = +25°C |
|-------------------|-------------------------------|----------------------------------------------|
| 30V               | 10mΩ @ V <sub>GS</sub> = 10V  | 13A                                          |
|                   | 15mΩ @ V <sub>GS</sub> = 4.5V | 11A                                          |

## Description

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

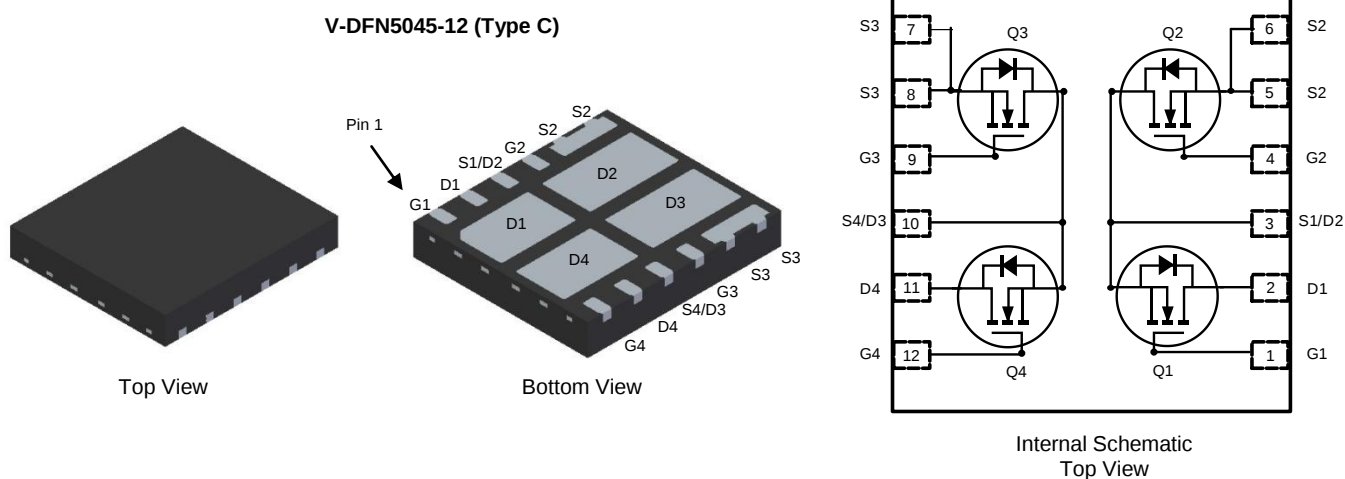
- High-Efficiency Bridge Rectifiers

## Features

- Low On-Resistance
- Low Input Capacitance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**

## Mechanical Data

- Case: V-DFN5045-12
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.056grams (Approximate)

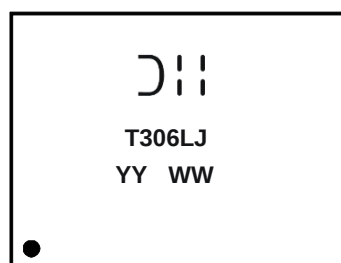


## Ordering Information (Note 4)

| Part Number    | Case                  | Quantity per Reel |
|----------------|-----------------------|-------------------|
| DMHT3006LFJ-13 | V-DFN5045-12 (Type C) | 3000              |

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



DII = Manufacturer's Marking  
T306LJ = Product Type Marking Code  
YYWW = Date Code Marking  
YY = Year (ex: 18 = 2018)  
WW = Week (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                          |              |                                                  | Symbol           | Value    | Unit |
|---------------------------------------------------------|--------------|--------------------------------------------------|------------------|----------|------|
| Drain-Source Voltage                                    |              |                                                  | V <sub>DSS</sub> | 30       | V    |
| Gate-Source Voltage                                     |              |                                                  | V <sub>GSS</sub> | ±20      | V    |
| Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V | Steady State | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | I <sub>D</sub>   | 13<br>10 | A    |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)      |              |                                                  | I <sub>DM</sub>  | 80       | A    |
| Continuous Source-Drain Diode Current (Note 6)          |              | T <sub>A</sub> = +25°C                           | I <sub>S</sub>   | 2        | A    |
| Avalanche Current (Note 7) L = 0.1mH                    |              |                                                  | I <sub>AS</sub>  | 23       | A    |
| Avalanche Energy (Note 7) L = 0.1mH                     |              |                                                  | E <sub>AS</sub>  | 28       | mJ   |

**Thermal Characteristics**

| Characteristic                                   |                        | Symbol                            | Value       | Unit |
|--------------------------------------------------|------------------------|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 5)                 | T <sub>A</sub> = +25°C | P <sub>D</sub>                    | 1.3         | W    |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State           | R <sub>θJA</sub>                  | 95          | °C/W |
| Total Power Dissipation (Note 6)                 | T <sub>A</sub> = +25°C | P <sub>D</sub>                    | 2.1         | W    |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State           | R <sub>θJA</sub>                  | 60          | °C/W |
| Thermal Resistance, Junction to Case (Note 6)    |                        | R <sub>θJC</sub>                  | 22          | °C/W |
| Operating and Storage Temperature Range          |                        | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                           | Symbol              | Min | Typ  | Max  | Unit | Test Condition                                                                               |
|----------------------------------------------------------|---------------------|-----|------|------|------|----------------------------------------------------------------------------------------------|
| <b>OFF CHARACTERISTICS (Note 8)</b>                      |                     |     |      |      |      |                                                                                              |
| Drain-Source Breakdown Voltage                           | BV <sub>DSS</sub>   | 30  | —    | —    | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA                                                 |
| Zero Gate Voltage Drain Current (T <sub>J</sub> = +25°C) | I <sub>DSS</sub>    | —   | —    | 1    | µA   | V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V                                                  |
| Gate-Source Leakage                                      | I <sub>GSS</sub>    | —   | —    | ±100 | nA   | V <sub>GS</sub> = +20V, V <sub>DS</sub> = 0V<br>V <sub>GS</sub> = -16V, V <sub>DS</sub> = 0V |
| <b>ON CHARACTERISTICS (Note 8)</b>                       |                     |     |      |      |      |                                                                                              |
| Gate Threshold Voltage                                   | V <sub>GS(TH)</sub> | 1.0 | —    | 3.0  | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA                                   |
| Static Drain-Source On-Resistance                        | R <sub>DS(ON)</sub> | —   | 5.8  | 10   | mΩ   | V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A                                                  |
|                                                          |                     |     | 7.8  | 15   |      | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 8A                                                  |
| Diode Forward Voltage                                    | V <sub>SD</sub>     | —   | 0.7  | 1.0  | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = 2A                                                    |
| <b>DYNAMIC CHARACTERISTICS (Note 9)</b>                  |                     |     |      |      |      |                                                                                              |
| Input Capacitance                                        | C <sub>iss</sub>    | —   | 1171 | —    | pF   | V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V,<br>f = 1.0MHz                                   |
| Output Capacitance                                       | C <sub>oss</sub>    | —   | 421  | —    |      |                                                                                              |
| Reverse Transfer Capacitance                             | C <sub>rss</sub>    | —   | 63   | —    |      |                                                                                              |
| Gate Resistance                                          | R <sub>g</sub>      | —   | 1.9  | —    | Ω    | V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz                                       |
| Total Gate Charge (V <sub>GS</sub> = 4.5V)               | Q <sub>g</sub>      | —   | 9.0  | —    | nC   | V <sub>DD</sub> = 15V, I <sub>D</sub> = 9A                                                   |
| Total Gate Charge (V <sub>GS</sub> = 10V)                | Q <sub>g</sub>      | —   | 17   | —    |      |                                                                                              |
| Gate-Source Charge                                       | Q <sub>gs</sub>     | —   | 2.7  | —    |      |                                                                                              |
| Gate-Drain Charge                                        | Q <sub>gd</sub>     | —   | 4.7  | —    |      |                                                                                              |
| Turn-On Delay Time                                       | t <sub>D(ON)</sub>  | —   | 7.4  | —    | ns   | V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V,<br>R <sub>g</sub> = 3Ω, I <sub>D</sub> = 9A    |
| Turn-On Rise Time                                        | t <sub>r</sub>      | —   | 54   | —    |      |                                                                                              |
| Turn-Off Delay Time                                      | t <sub>D(OFF)</sub> | —   | 16   | —    |      |                                                                                              |
| Turn-Off Fall Time                                       | t <sub>f</sub>      | —   | 4.3  | —    |      |                                                                                              |
| Reverse Recovery Time                                    | t <sub>RR</sub>     | —   | 18   | —    | ns   | I <sub>F</sub> = 1.5A, di/dt = 100A/µs                                                       |
| Reverse Recovery Charge                                  | Q <sub>RR</sub>     | —   | 8.5  | —    | nC   |                                                                                              |

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  7. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  8. Short duration pulse test used to minimize self-heating effect.
  9. Guaranteed by design. Not subject to product testing.

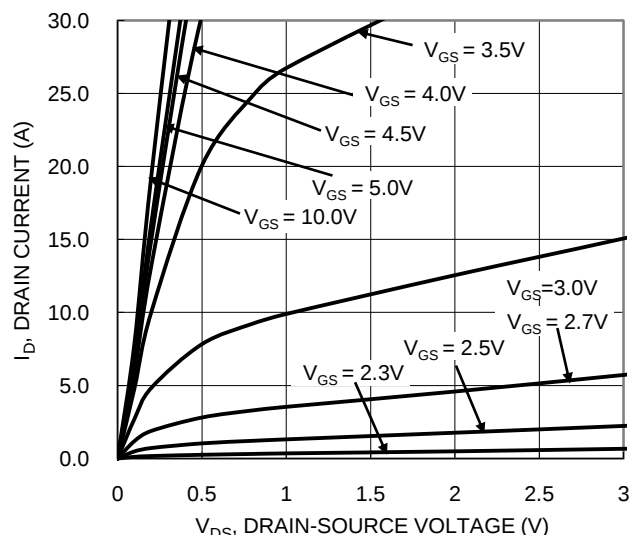


Figure 1. Typical Output Characteristic

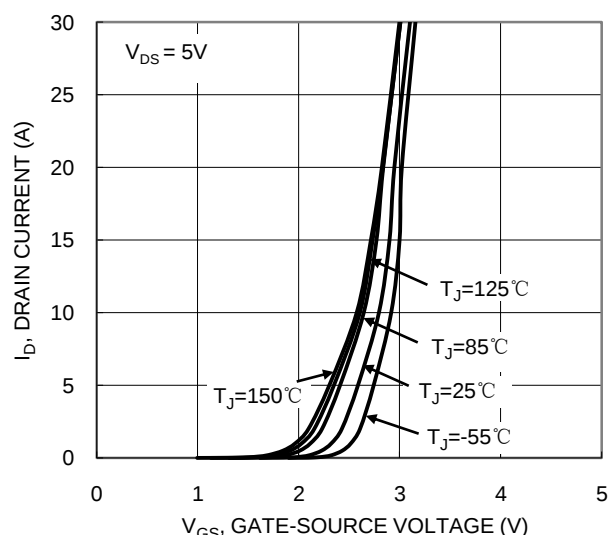


Figure 2. Typical Transfer Characteristic

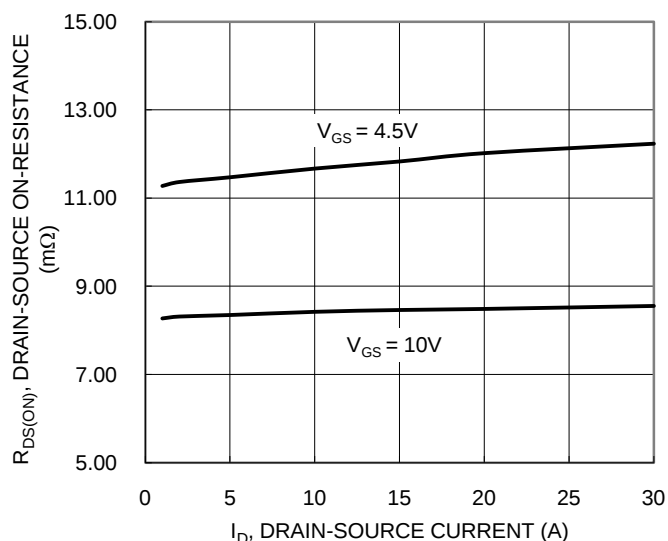


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

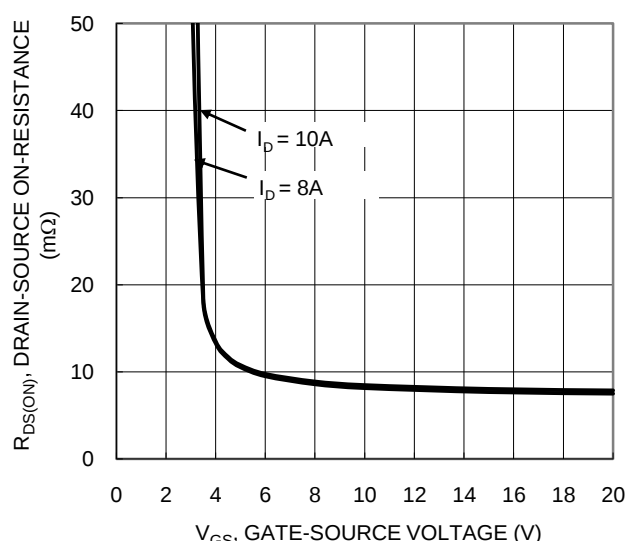


Figure 4. Typical Transfer Characteristic

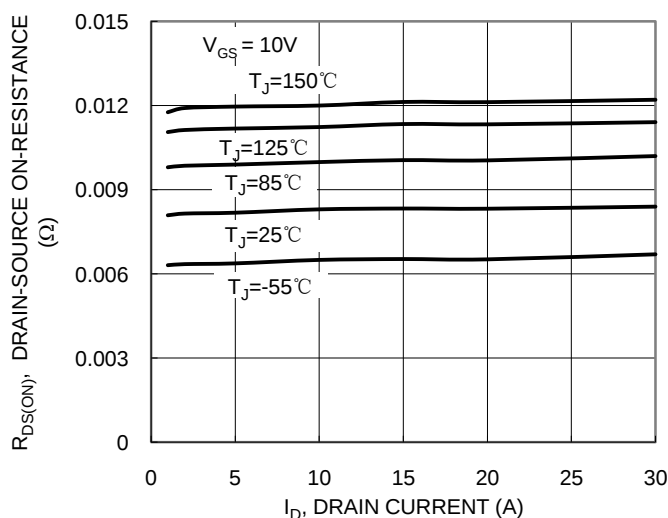


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

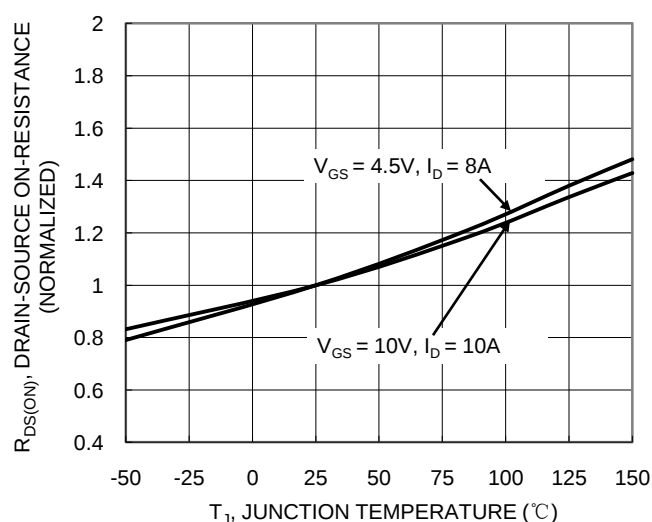


Figure 6. On-Resistance Variation with Temperature

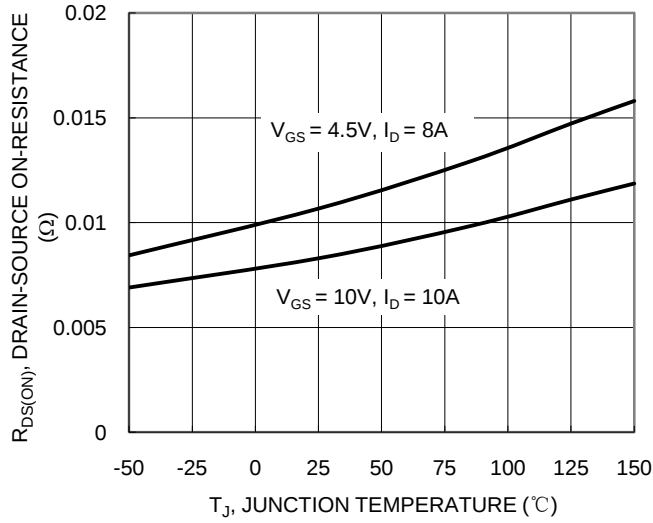


Figure 7. On-Resistance Variation with Temperature

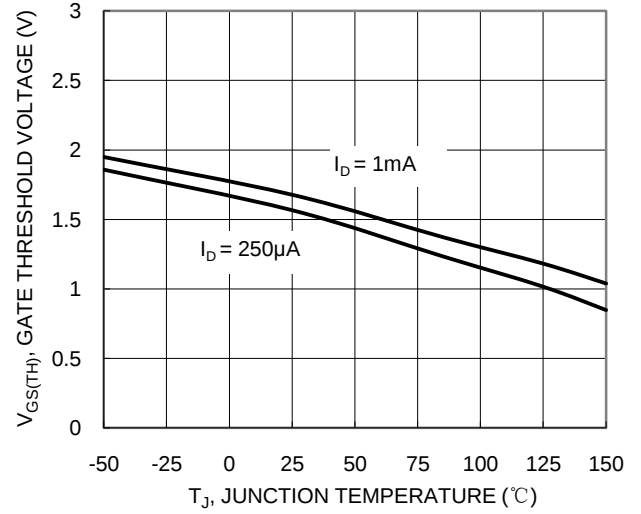


Figure 8. Gate Threshold Variation vs. Junction Temperature

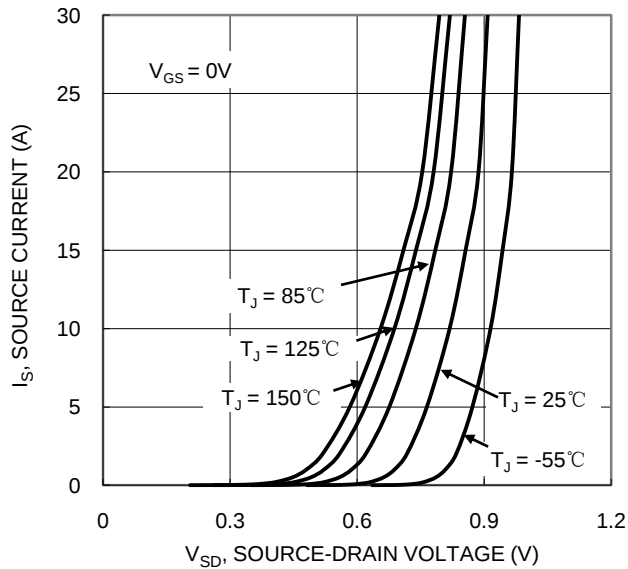


Figure 9. Diode Forward Voltage vs. Current

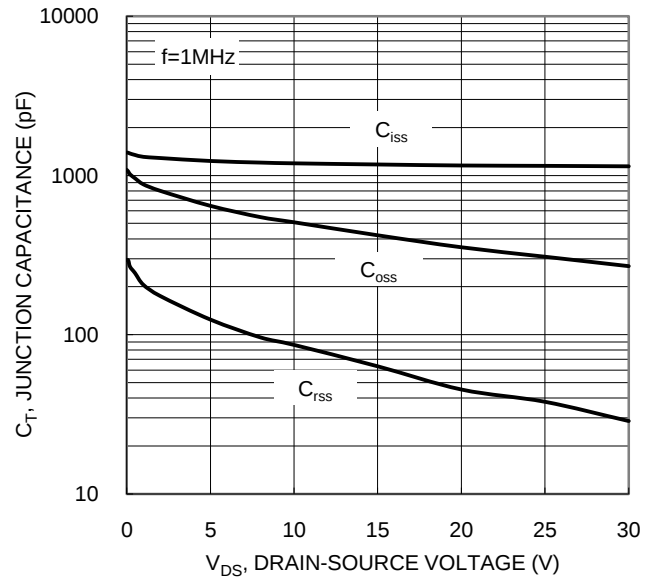


Figure 10. Typical Junction Capacitance

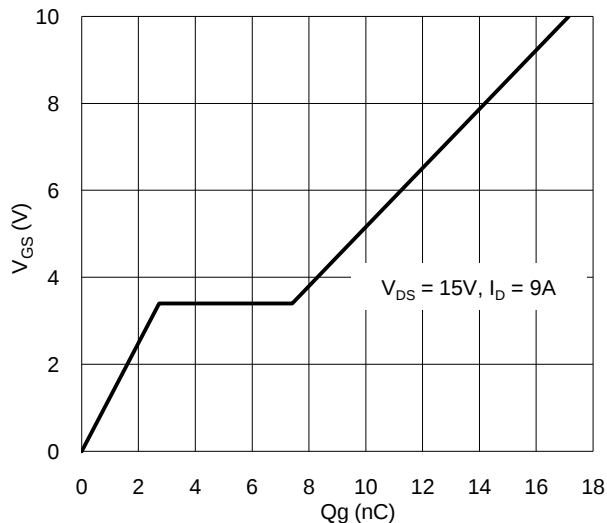


Figure 11. Gate Charge

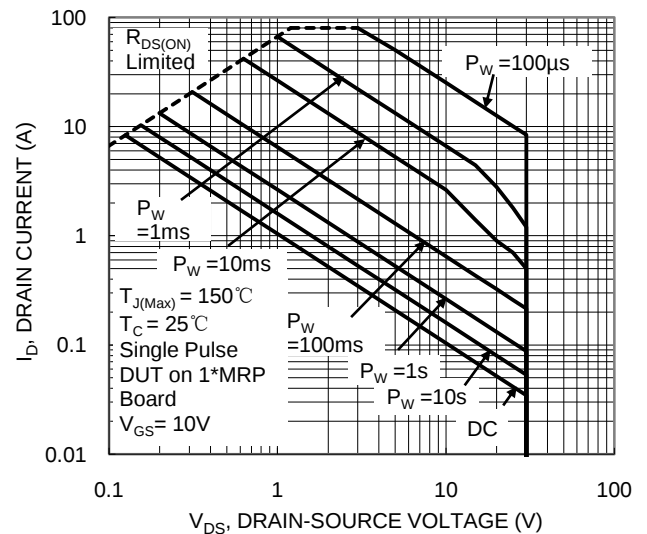


Figure 12. SOA, Safe Operation Area

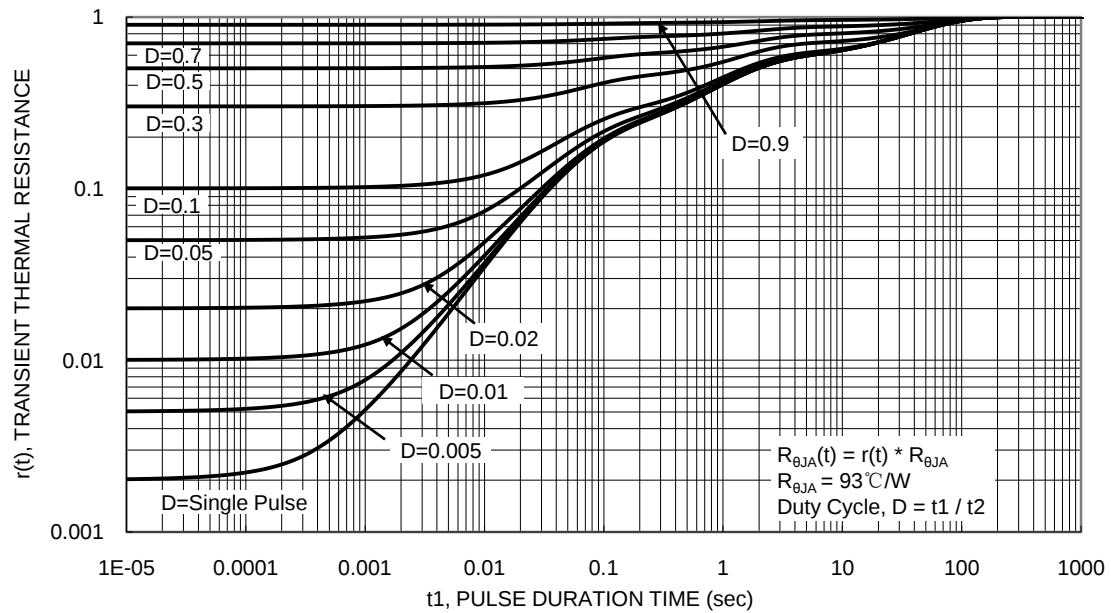
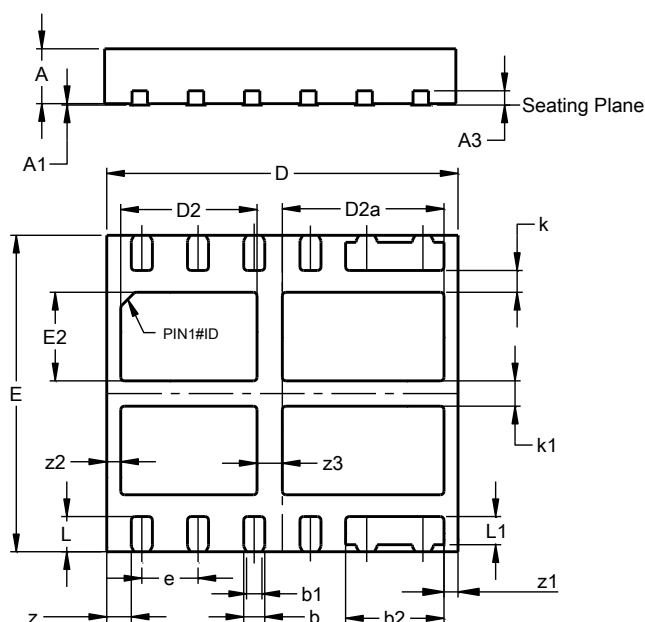


Figure 13. Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**V-DFN5045-12 (Type C)**

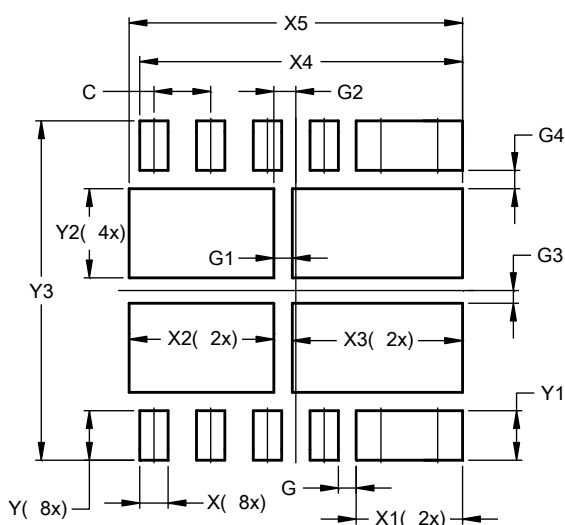


| V-DFN5045-12<br>(Type C) |      |      |       |
|--------------------------|------|------|-------|
| Dim                      | Min  | Max  | Typ   |
| A                        | 0.75 | 0.85 | 0.80  |
| A1                       | 0.00 | 0.05 | 0.02  |
| A3                       | --   | --   | 0.203 |
| b                        | 0.25 | 0.35 | 0.30  |
| b1                       | 0.17 | 0.27 | 0.22  |
| b2                       | 1.35 | 1.45 | 1.40  |
| D                        | 4.95 | 5.05 | 5.00  |
| D2                       | 1.84 | 2.04 | 1.94  |
| D2a                      | 2.20 | 2.40 | 2.30  |
| e                        | --   | --   | 0.80  |
| E                        | 4.45 | 4.55 | 4.50  |
| E2                       | 1.16 | 1.36 | 1.26  |
| k                        | --   | --   | 0.31  |
| k1                       | --   | --   | 0.36  |
| L                        | 0.45 | 0.55 | 0.50  |
| L1                       | 0.35 | 0.45 | 0.40  |
| z                        | --   | --   | 0.35  |
| z1                       | --   | --   | 0.20  |
| z2                       | --   | --   | 0.20  |
| z3                       | --   | --   | 0.36  |
| All Dimensions in mm     |      |      |       |

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**V-DFN5045-12 (Type C)**



| Dimensions | Value<br>(in mm) |
|------------|------------------|
| C          | 0.800            |
| G          | 0.250            |
| G1         | 0.260            |
| G2         | 0.310            |
| G3         | 0.180            |
| G4         | 0.260            |
| X          | 0.400            |
| X1         | 1.500            |
| X2         | 2.040            |
| X3         | 2.400            |
| X4         | 4.550            |
| X5         | 4.700            |
| Y          | 0.700            |
| Y1         | 0.700            |
| Y2         | 1.260            |
| Y3         | 4.800            |

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